

RoHS Compliant Product
A suffix of "C" specifies halogen & lead-free

FEATURES

- Low on-resistance
- Fast switching speed
- Drive circuits can be simple
- Parallel use is easy
- Low voltage drive makes this device ideal for portable equipment

APPLICATION

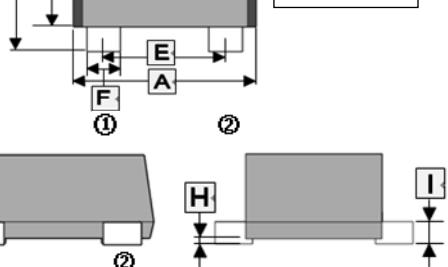
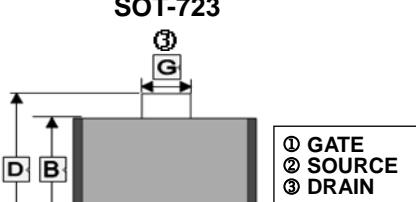
- Interfacing
- Switching

MARKING

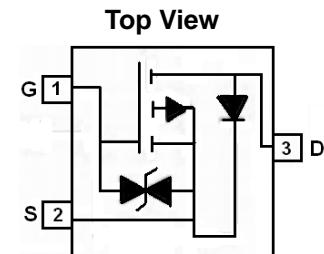
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PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-723	8K	7 inch



REF.	Millimeter	REF.	Millimeter
	Min.		Max.
A	1.150	F	0.170
B	0.750	G	0.270
C	-	H	0
D	1.150	I	-
E	0.800TYP.		



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 6	V
Continuous Drain Current ¹	I_D	-0.66	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	-1.2	A
Total Power Dissipation ¹	P_D	150	mW
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	833	$^\circ\text{C} / \text{W}$
Lead Temperature for Soldering Purposes (1/8" from case for 10S)	T_L	260	$^\circ\text{C}$
Operating Junction & Storage Temperature Range	T_J, T_{STG}	150, -55~150	$^\circ\text{C}$

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise specified)

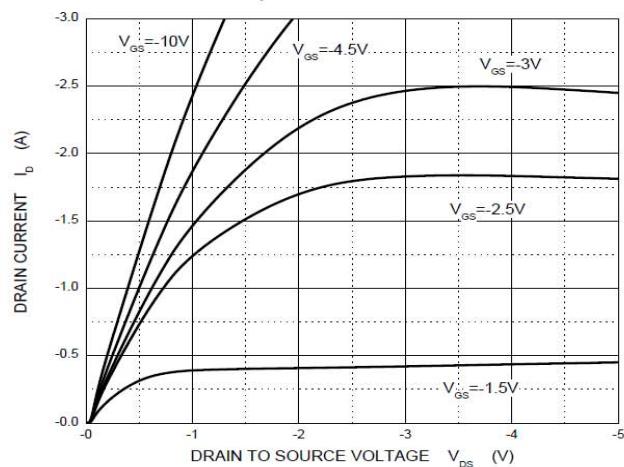
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-20	-	-	V	$V_{GS}=0$, $I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS} = -20V$, $V_{GS}=0$
Gate-Body Leakage Current	I_{GSS}	-	-	± 20	μA	$V_{DS}=0$, $V_{GS}=\pm 12V$
Gate Threshold Voltage ¹	$V_{GS(th)}$	-0.35	-	-0.8	V	$V_{DS}=V_{GS}$, $I_D = -250\mu A$
Drain-Source On-Resistance ¹	$R_{DS(ON)}$	-	-	520	$m\Omega$	$V_{GS} = -4.5V$, $I_D = 1A$
		-	-	700		$V_{GS} = -2.5V$, $I_D = -0.8A$
		-	-	950		$V_{GS} = -1.8V$, $I_D = -0.5A$
Forward Transconductance ¹	g_{fs}	-	1.2	-	S	$V_{DS} = -10V$, $I_D = -0.54A$
Diode forward voltage	V_{SD}	-	-	-1.2	V	$I_S = -0.5A$, $V_{DS}=0$
Dynamic Characteristics ³						
Input Capacitance	C_{iss}	-	113	-	pF	$V_{DS} = -16V$, $V_{GS}=0$, $f=1MHz$
Output Capacitance	C_{oss}	-	15	-		
Reverse Transfer Capacitance	C_{rss}	-	9	-		
Switching Characteristics ³						
Turn-On Delay Time ²	$T_{d(on)}$	-	9	-	nS	$V_{DS} = -10V$, $I_D = -200mA$, $V_{GS} = -4.5V$, $R_{GEN} = 10\Omega$
Rise Time ²	T_r	-	5.8	-		
Turn-Off Delay Time ²	$T_{d(off)}$	-	32.7	-		
Fall Time ²	T_f	-	20.3	-		

Notes:

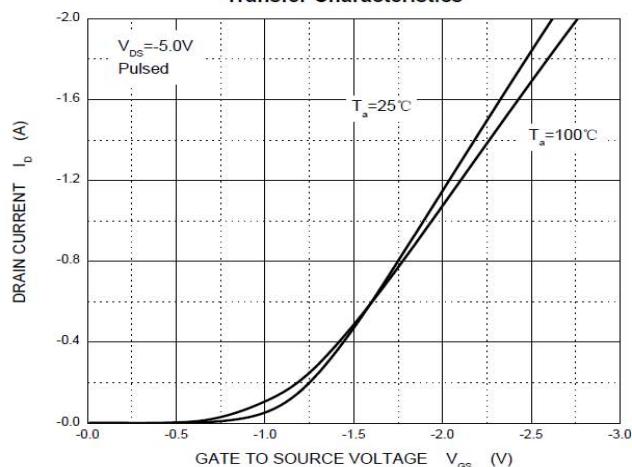
1. Pulse Test : Pulse Width=300μs, Duty Cycle=2%.
2. Switching characteristics are independent of operating junction temperatures.
3. Guaranteed by design, not subject to producting.

Typical Characteristics

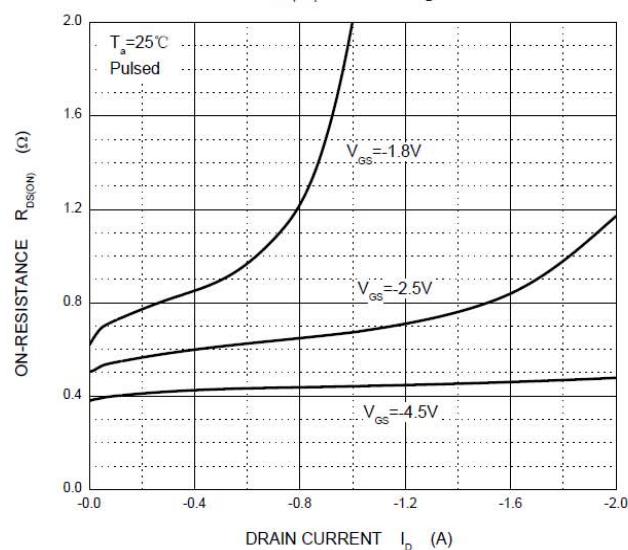
Output Characteristics



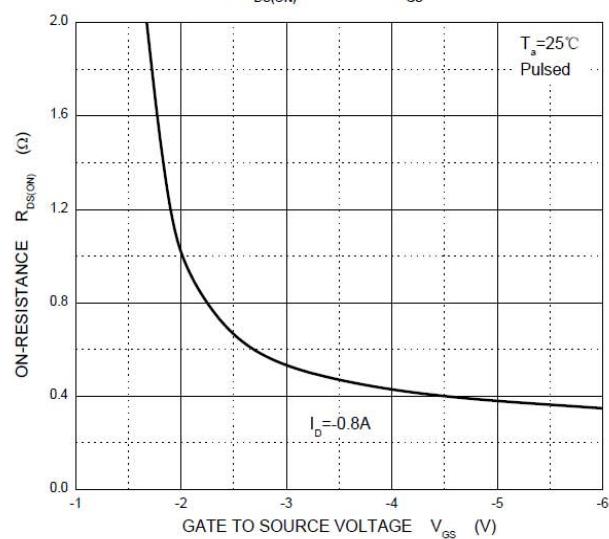
Transfer Characteristics



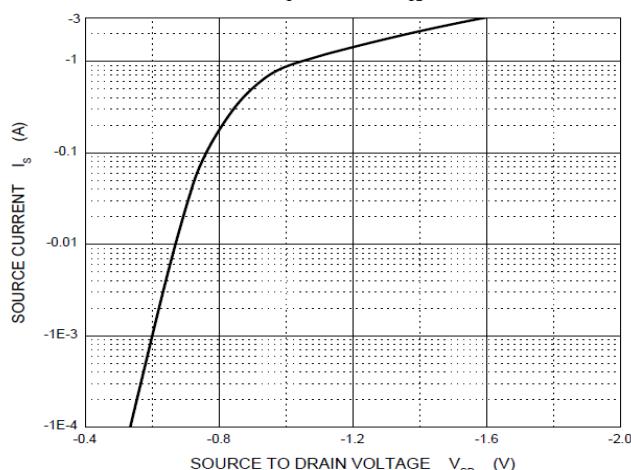
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



Threshold Voltage

